## **Supporting information**

Planar Heterojunction (PHJ) Solar Cell Employing Single Source Precursor Solution Processed Sb<sub>2</sub>S<sub>3</sub> Thin Film as the Light Absorber

Muthusamy Tamilselvan<sup>1</sup>, Archana Byregowda<sup>2</sup>, Ching-Yuan Su<sup>3</sup>, Chung-Jen Tseng<sup>4</sup>, and Aninda J. Bhattacharyya<sup>1</sup>\*

<sup>1</sup>Solid State and Structural Chemistry Unit, Indian Institute of Science, Bengaluru 560012,

India

<sup>2</sup>Jawaharlal Nehru Technological University, Department of Chemistry, Ananthpur Hyderabad, 500085, India

<sup>3</sup>Graduate Institute of Energy Engineering, National Central University, Taoyuan City 32001,

Taiwan

<sup>4</sup>Department of Mechanical Engineering/ Institute of Energy Engineering, National Central University, Taoyuan City 32001, Taiwan

<sup>&</sup>lt;sup>2</sup> Present address: Solid State and Structural Chemistry Unit, Indian Institute of Science, Bengaluru 560012, India

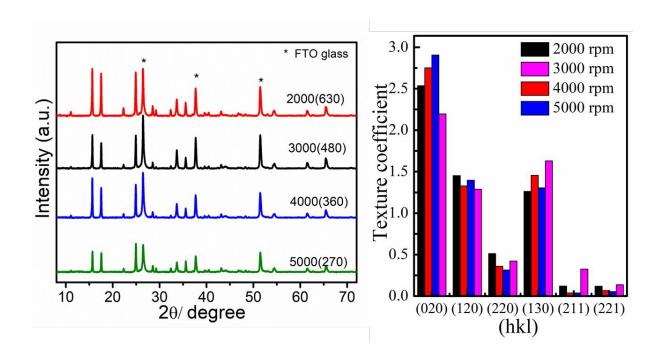


Figure S1. XRD patterns and texture coefficient of  $Sb_2S_3$  film of different thickness sintered at 350 ° C

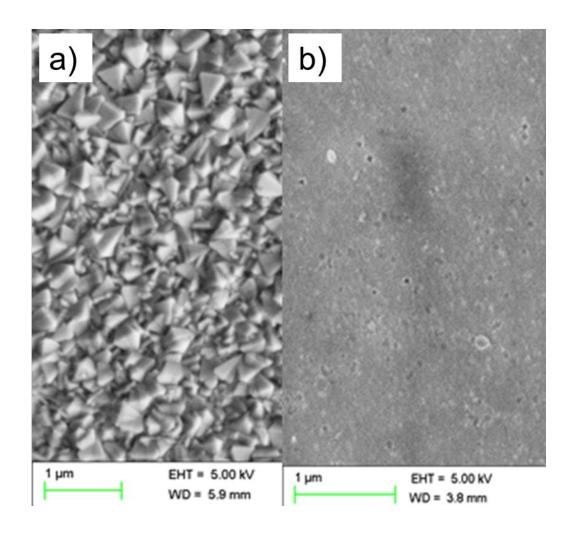


Figure S2. FESEM images of a) bare FTO glass, b) CdS coated FTO glass

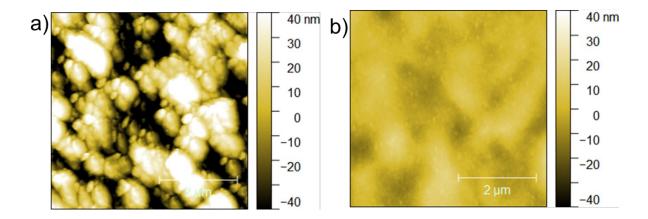
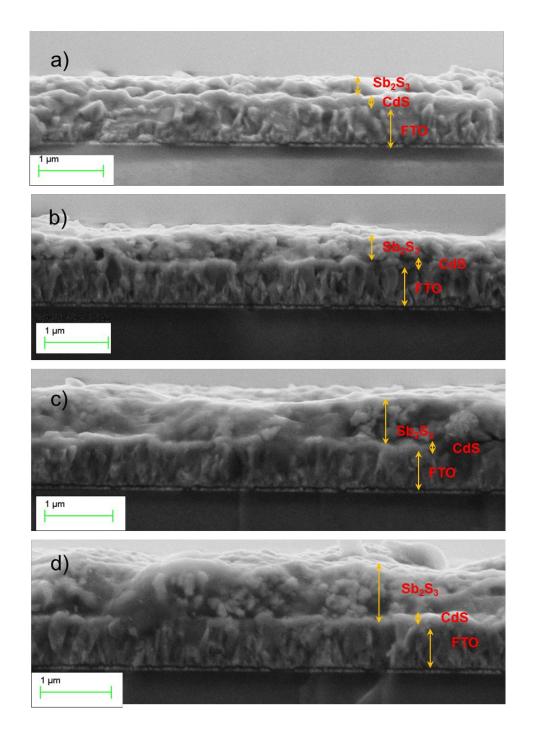


Figure S3. a) AFM images of a) bare FTO glass, b) CdS coated FTO glass



**Figure S4.** Cross section of FESEM images of deposited Sb<sub>2</sub>S<sub>3</sub> on CdS/FTO glass at different spin rate. a) 5000, b) 4000, c) 3000 and d) 2000 rpm.

**Table S1.** Elemental analysis (EDS) of  $Sb_2S_3$  films deposited on bare glass substrate. The theoretical concentration ratio between sulphur and antimony is 1.5. Sample at 275 and 300°C are show slightly higher sulphur concentration, and samples sintered at 325 and 350°C shows lower deficiency in sulphur.

Temperature (°C)	S(%)	Sb(%)	Ratio(S/Sb)
275	61.7	38.3	1.610
300	60.41	39.58	1.526
325	59.74	40.255	1.484
350	58.55	41.44	1.412

**Table S2.** The average photovoltaic device parameters of five solar cells for optimum sintering temperature (350° C) and film thickness (480 nm). Standard deviation values are given inside the parentheses.

sintering temperature 350° C							
V <sub>oc</sub>	$J_{SC}$	FF	PCE (%)	$R_{Sh}$	$R_{S}$		
(V)	(mAcm <sup>-2</sup> )			(ohm cm <sup>2</sup> )	(ohm cm <sup>2</sup> )		
0.52(0.004)	8.2(0.32)	0.38(0.02)	1.62(0.08)	182(46.7)	32(2.1)		
Spinning speed/ Film thickness ( 3000rpm/480 nm)							
0.52(0.001)	9.4(0.13)	0.48(0.007)	2.35(0.045)	391(46.5)	18(1.9)		